

Progress on Low Power FEE ASIC Development for TPC

Wei Liu^{1,2}, Xinyuan Zhao^{1,2}, Zhi Deng^{1,2}, Fule Li³, Xian Gu³, Yulan Li^{1,2}, Huirong Qi⁴

¹ Department of Engineering Physics, Tsinghua University, Beijing, China

²Key Laboratory of Particle & Radiation Imaging, Ministry of Education, Beijing, China

³Institute of Microelectronics, Tsinghua University, Beijing, China

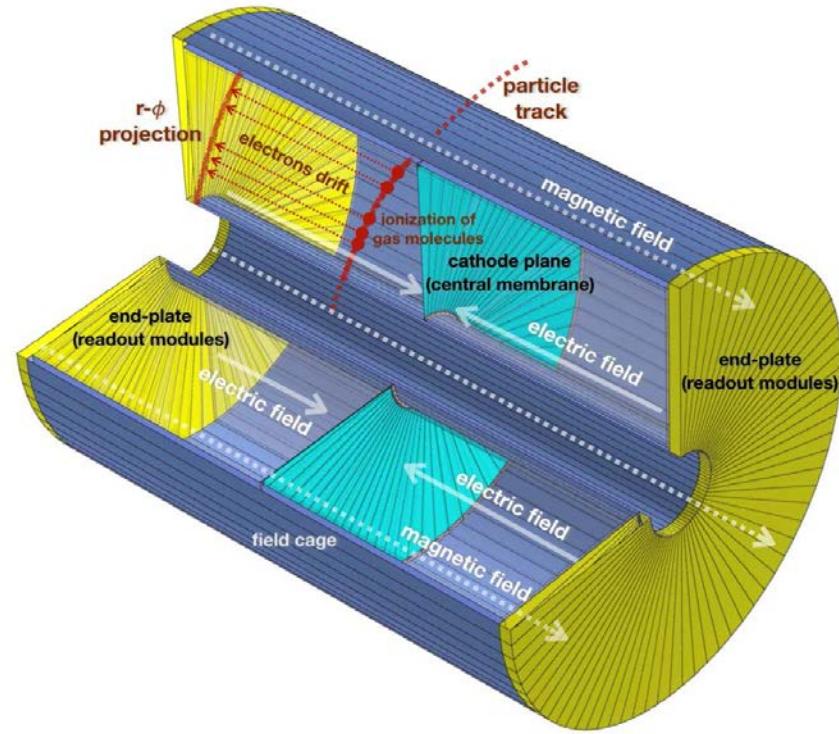
⁴Institute of High Energy Physics, Chinese Academy of Science, Beijing, China



Outline

- Introduction
- Progress on ASIC Design
- Progress on Digital Filters and Data Compression
- Summary & Future Plan

Introduction



Momentum resolution (B=3.5T)	$\delta(1/p_t \approx 10^{-4}/GeV/c)$
δ_{point} in $r\Phi$	<100 μm
δ_{point} in rz	0.4-1.4 mm
Inner radius	329 mm
Outer radius	1800 mm
Drift length	2350 mm
TPC material budget	$\approx 0.05X_0$ incl. field cage $< 0.25X_0$ for readout endcap
Pad pitch/no. padrows	$\approx 1 mm \times (4\sim10mm) / \approx 200$
2-hit resolution	$\approx 2 mm$
Efficiency	>97% for TPC only ($p_t > 1GeV$) >99% all tracking ($p_t > 1GeV$)

- TPC can provide large-volume high-precision 3D track measurement with stringent material budget
- In order to achieve high spatial resolution, small pads (e.g. 1 mm x 6mm) are needed, resulting **~1 million** channel of readout electronics
- Need low power consumption readout electronics **working at continuous mode**

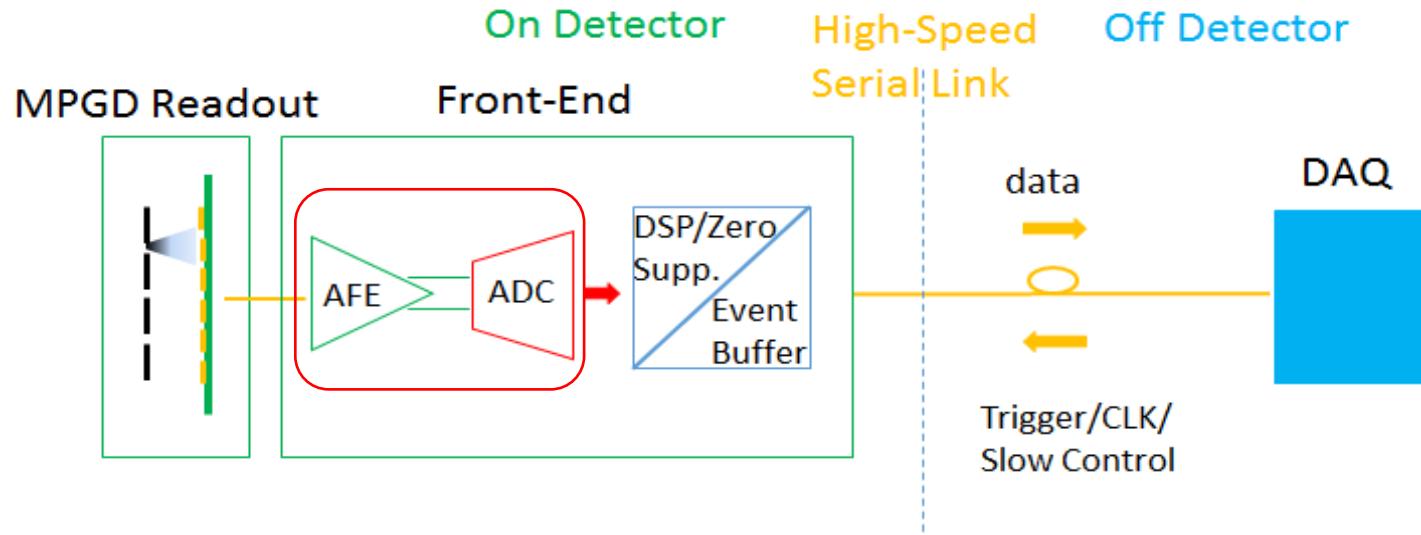
Current TPC Readout ASICs

	PASA/ALTRO	AGET	Super-ALTRO	SAMPA
TPC	ALICE	T2K	ILC	ALICE upgrade
Pad size	4x7.5 mm ²	6.9x9.7 mm ²	1x6 mm ²	4x7.5 mm ²
Pad channels	5.7 x 10 ⁵	1.25 x 10 ⁵	1-2 x 10 ⁶	5.7 x 10 ⁵
Readout Chamber	MWPC	MicroMegas	GEM/MicroMegas	GEM
Gain	12 mV/fC	0.2-17 mV/fC	12-27 mV/fC	20/30 mV/fC
Shaper	CR-(RC) ⁴	CR-(RC) ²	CR-(RC) ⁴	CR-(RC) ⁴
Peaking time	200 ns	50 ns-1us	30-120 ns	80/160 ns
ENC	385 e	850 e @ 200ns	520 e	482 e @ 180ns
Waveform Sampler	ADC	SCA	ADC	ADC
Sampling frequency	10 MSPS	1-100 MSPS	40 MSPS	20 MSPS
Dynamic range	10 bit	12 bit(external)	10 bit	10 bit
Power consumption	32 mW/ch	10.0 mW/ch	47.3 mW/ch	8 mW/ch
CMOS Process	250 nm	350 nm	130 nm	130 nm

No current chips can meet the readout requirement for the CEPC TPC

- More advanced 65nm process
- Adopt simplified circuit structure such as SAR-ADC,CR-RC shaper

Architecture and Specifications of FEE

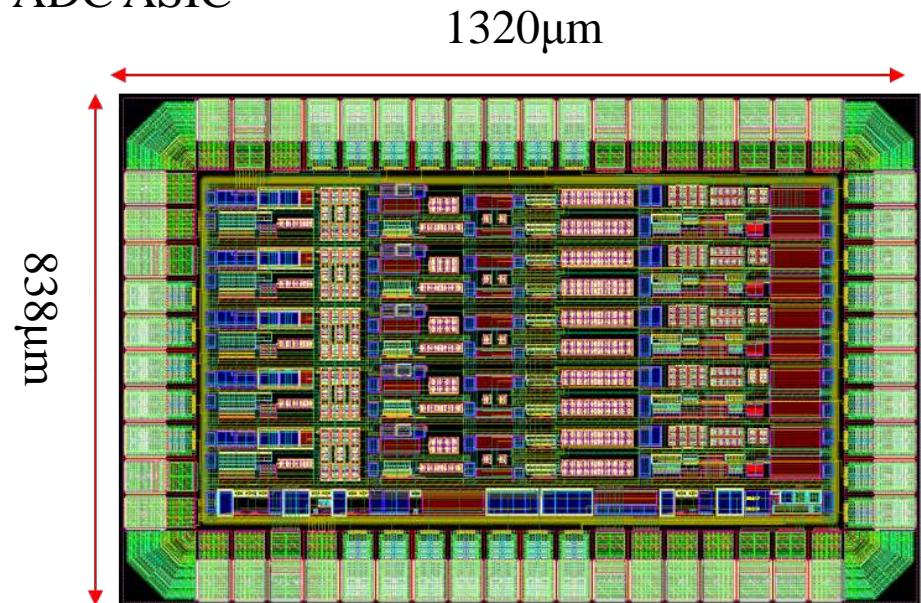
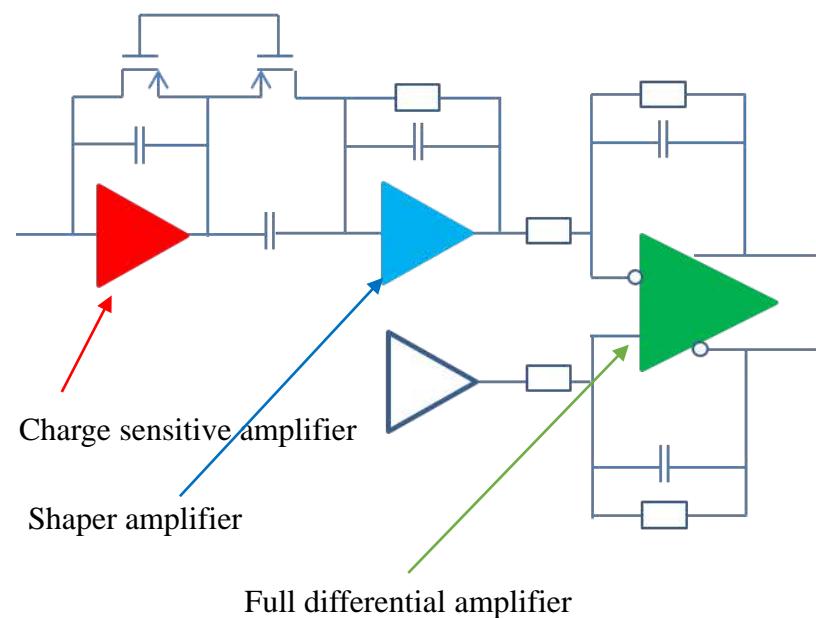


AFE(Analog Front-End)		SAR-ADC	
Signal Polarity	Negative	Input Range	-0.6 V ~ 0.6 V diff.
Detector Capacitance	5-20 pF	Resolution	10 bit
Shaper	CR-RC	Sampling Rate	40 MS/s
Shaping Time	160 ns	DNL	<0.6 LSB
ENC (Equivalent Noise Charge)	<500 e @ 10pF	INL	<0.6 LSB
Dynamic Range	120 fC	SFDR @ 2MHz, 40MSPS	68 dBc
Gain	10 mV/fC	SINAD	57 dB
INL (Integrated Non-Linearity)	<1%	ENOB	>9.2 bit @ 2MHz
Crosstalk	<1%	Power Consumption (ADC)	
Power Consumption (AFE)	<2.5 mW/ch	<2.5 mW/ch	

Current Status : Analog Front-End ASIC

Three prototype chips have been taped out and evaluated during 2017→ 2018

- 5 channel Analog Front-End ASIC
- Single channel SAR-ADC ASIC
- Single channel Analog Front-End +SAR-ADC ASIC



The test results of main specifications of 5 channel Analog Front-End ASIC:

- Power consumption: 2.02 mW/channel
- Gain: 9.8 mV/fC
- ENC(equivalent noise charge): 589 e @10pF

Current Status :TID Tests for Analog Front-End

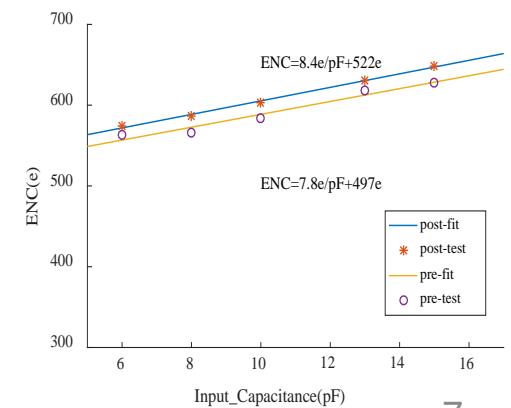
Test setup:

- Radiation Source: Co-60
- Does rate: 50 rad(Si)/s
- TID(total ionizing dose): 1 Mrad (Si)
- Sample no.: 3
- Chip working condition: 1.2 V supply voltage with 25 uA mater bias current

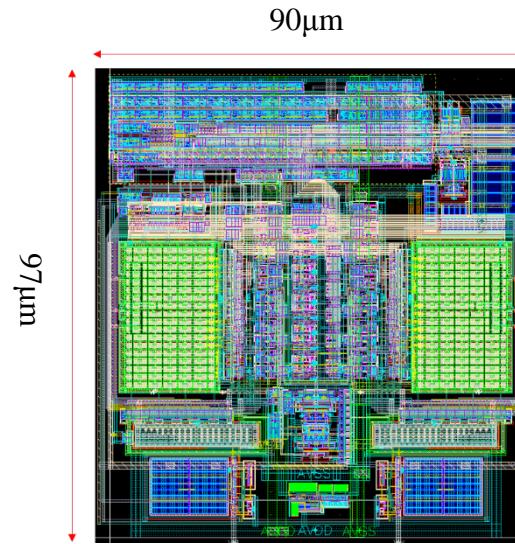
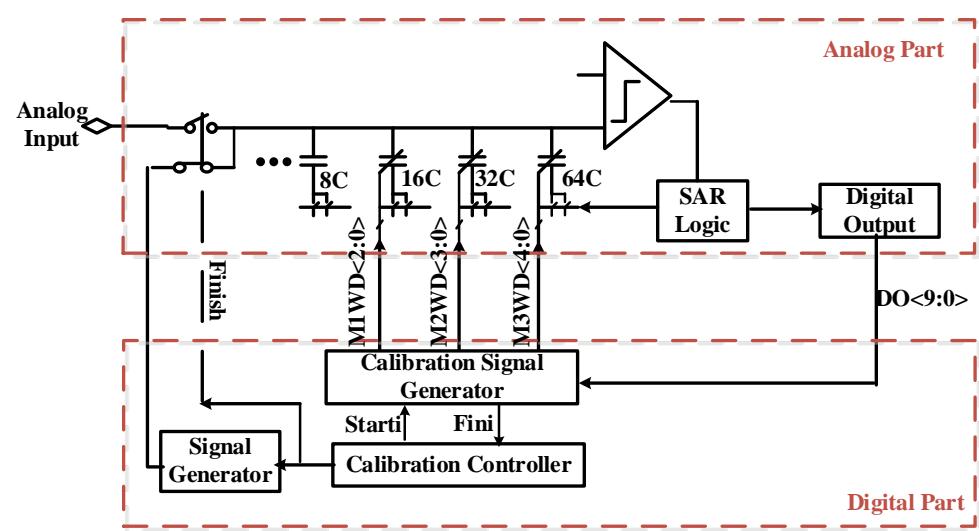


TID test results:

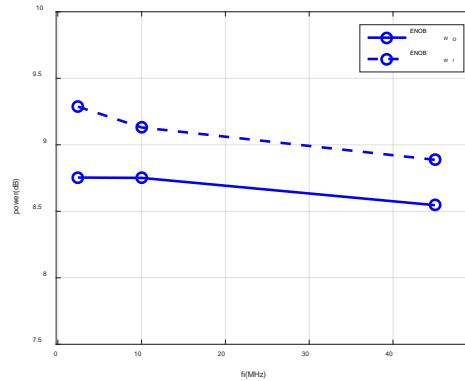
- The power consumption remained basically unchanged before and after TID test.
- The gain increased slightly ($9.8 \text{ mV/fC} \rightarrow 10.4 \text{ mV/fC}$) and the maximum integral non-linearity of there chips remained basically unchanged.
- The ENC increased slightly ($589 \text{ e} \rightarrow 605 \text{ e} @ 10\text{pF}$) before and after TID test.



Current Status : SAR ADC



Module Name	Power(mW)
Chip	4.0
Referred Buffer Module	0.25
SAR ADC Core Module	1.0
Clock Generation Module , etc	2.75



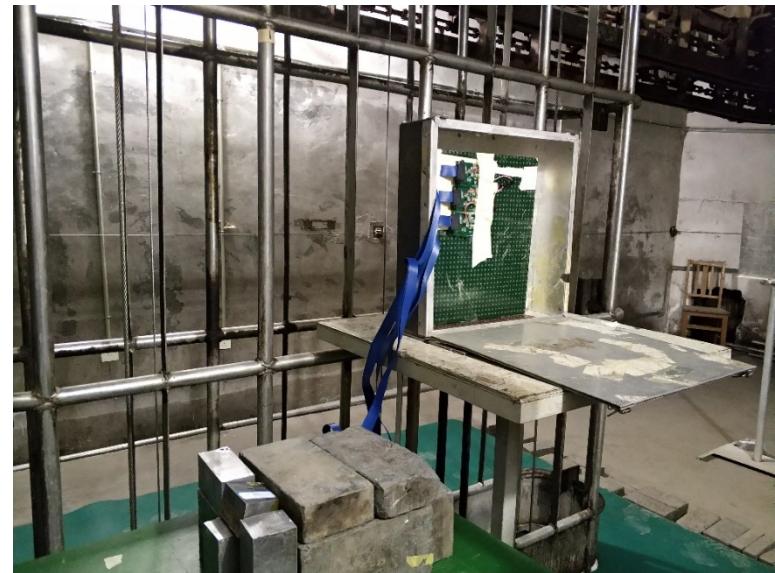
The test results of main specifications of single SAR ADC

- The core power consumption of SAR ADC: 1 mW
- Maximum INL(integral non-linearity),DNL(differential nonlinearity)=0.6 LSB
- ENOB=9.15 bit under 50 MS/s sampling rate with 2.4 MHz differential sinewave input

Current Status : TID Tests for SAR ADC

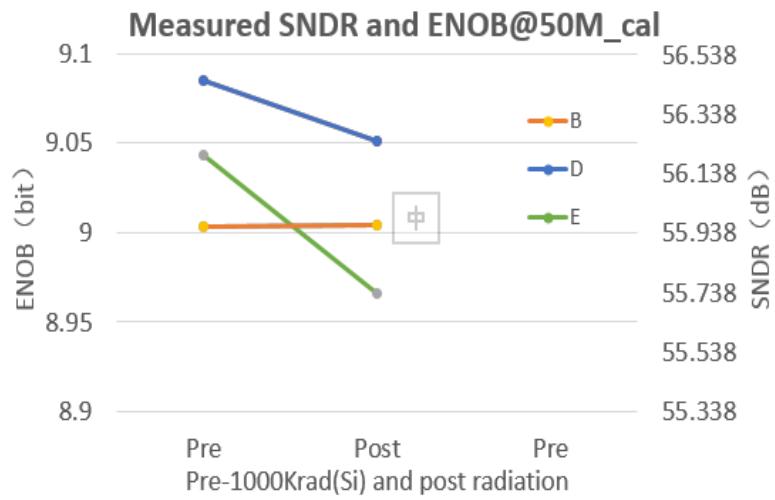
Test setup:

- Radiation Source: Co-60
- Dose rate: 50 rad(Si)/s
- TID: 1Mrad (Si)
- Sample no.: 3
- Chip working condition: CLK=50 M, fed with 2.4 MHz sine input signal

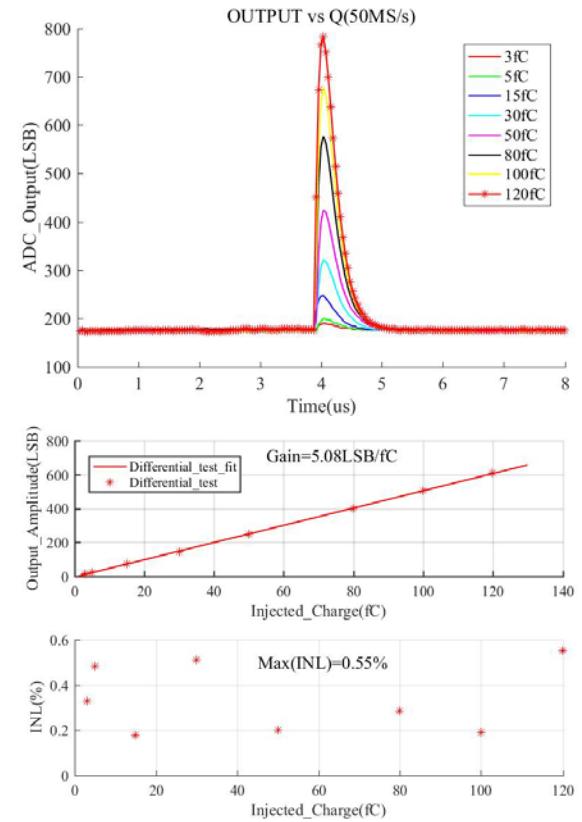
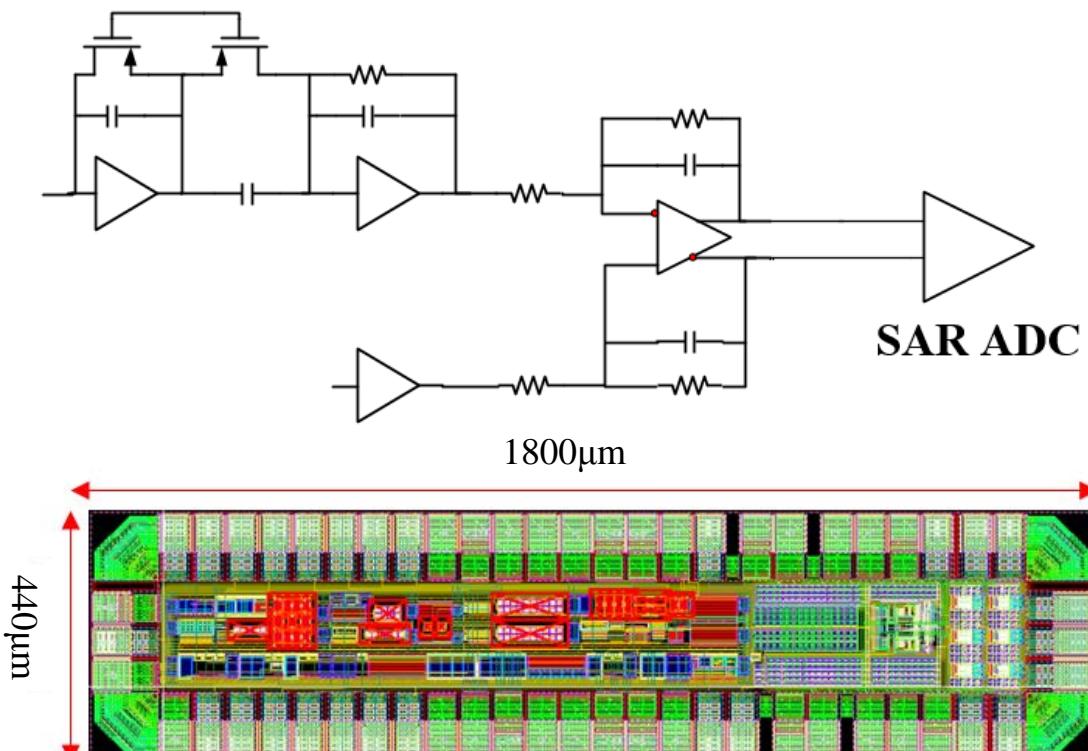


TID test results:

- The ENOB decreased slightly before and after TID test.
- The INL and DNL remained basically unchanged before and after TID test.



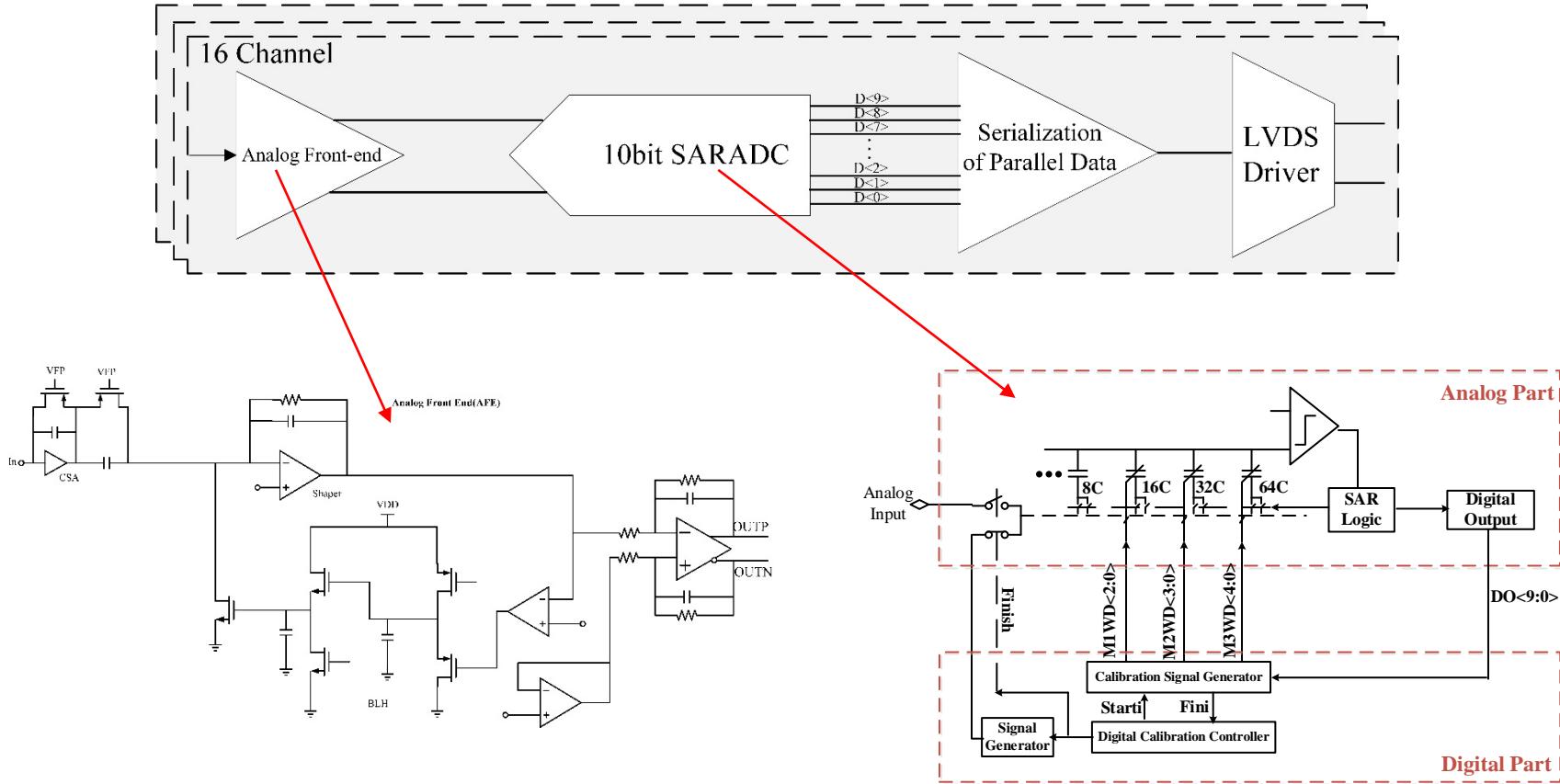
Current Status : Analog Front-End + SAR ADC



The test results of main specifications of single Analog Front-End + SARADC

- Power consumption: 2.5 mW
- gain: 5.08 LSB/fC
- ENC: 900 e @ 10pF

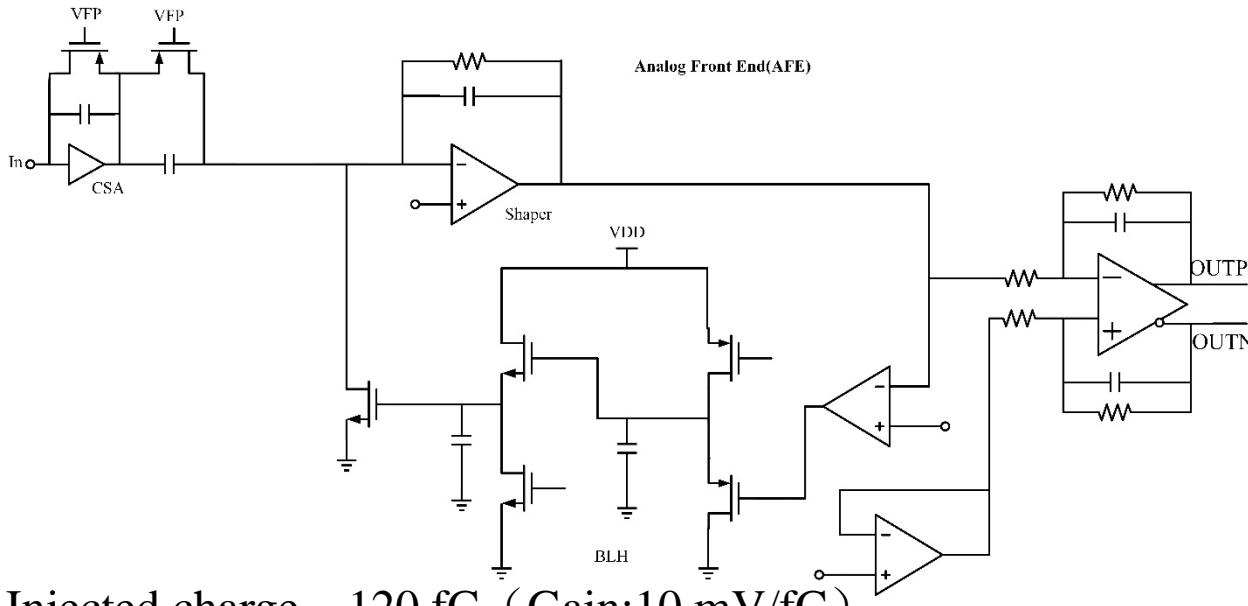
The 16-ch TPC Readout ASIC



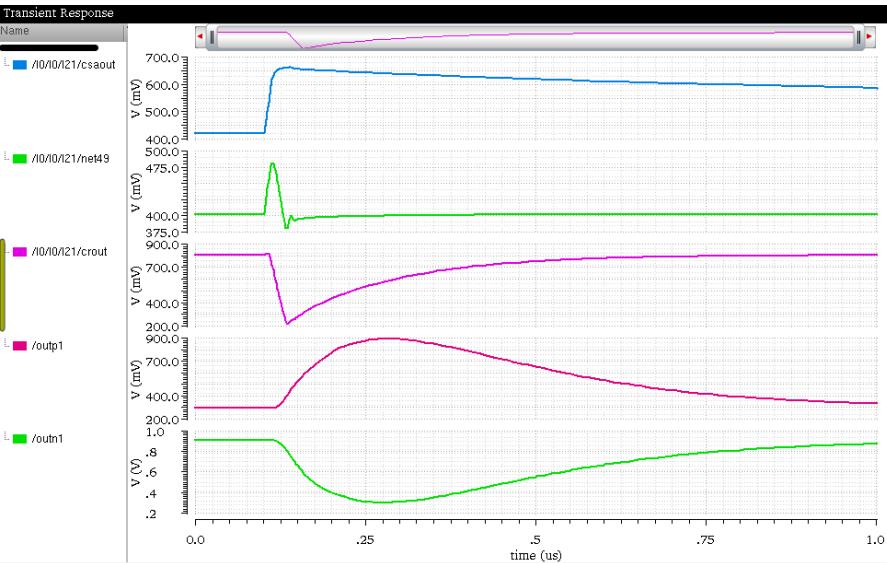
Design highlights:

- 16 channel
- Power consumption of Analog Front-end : from 2.02 mW/channel to 1.4 mW/channel
- ENC : from 589 e to 303 e @10 pF

Transient Simulation of Analog Front-End



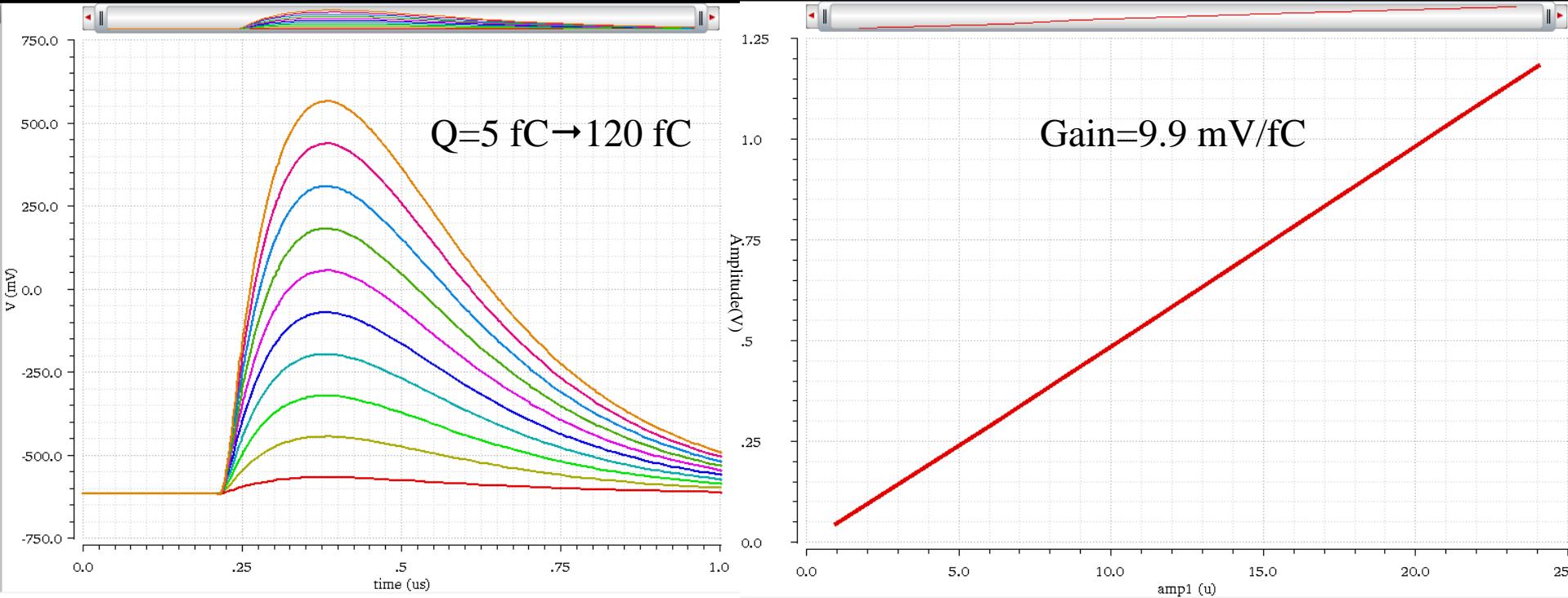
Injected charge: 120 fC (Gain: 10 mV/fC)



The simulation power consumption of Analog Front-end: **1.4 mW/channel**

The test power consumption of 5 channel Analog Front-end: 2.02 mW/channel

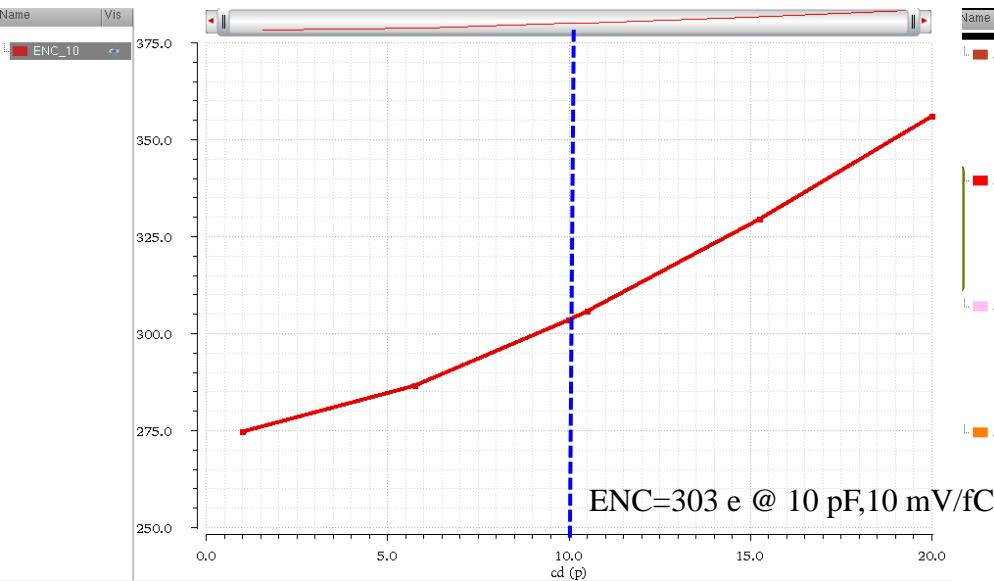
Linearity Simulation of Analog Front-End



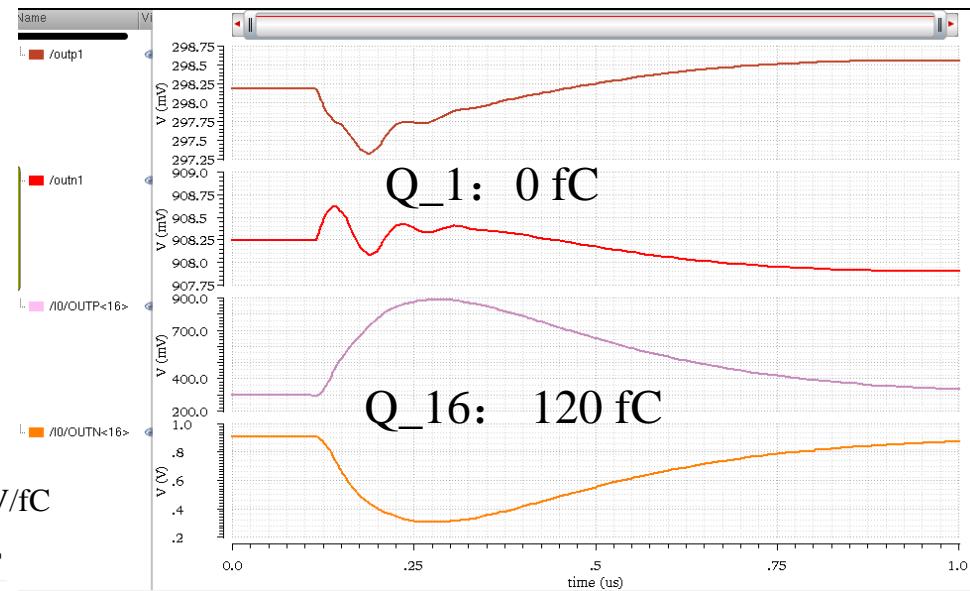
Gain(design value)	mV/fC	10	20	40
Gain (simulation value)	mV/fC	9.9	19.5	29.2

ENC and Crosstalk Simulation of Analog Front-End

- ENC



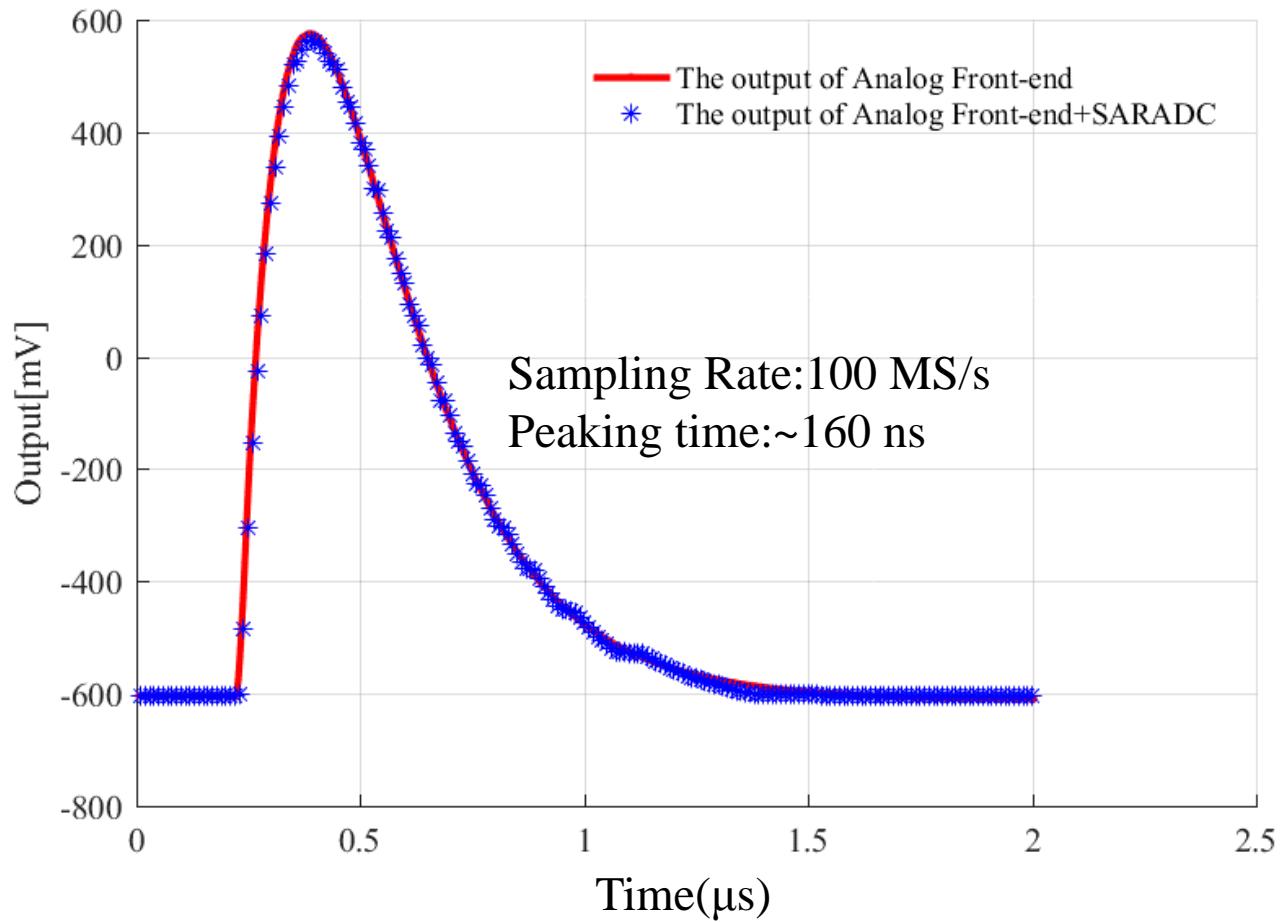
- Crosstalk



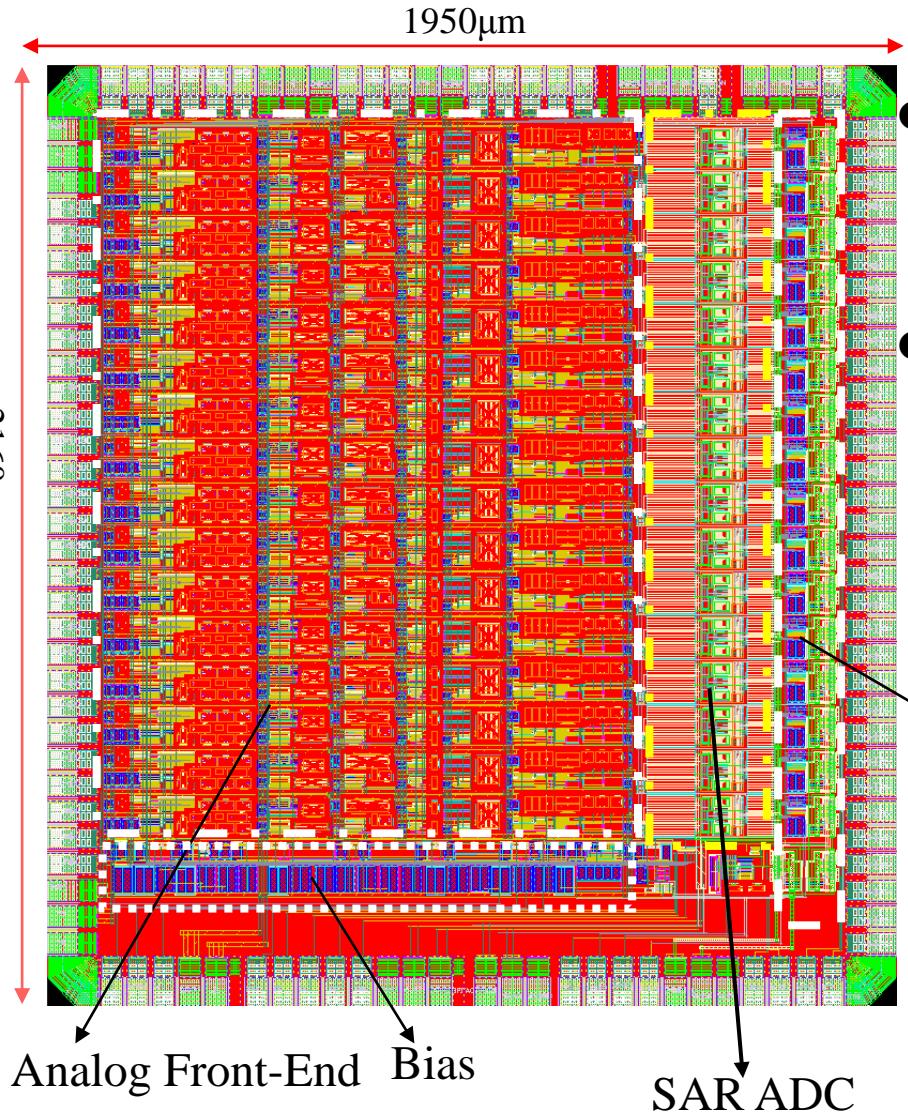
Gain mV/fC	10	20	30	40
ENC e @10 pF	303	189	159	146

$$\text{Crosstalk: } \frac{1.526 \text{ mV}}{1196 \text{ mV}} = 0.12\% < 1\%$$

Transient Simulation of TPC Readout ASIC



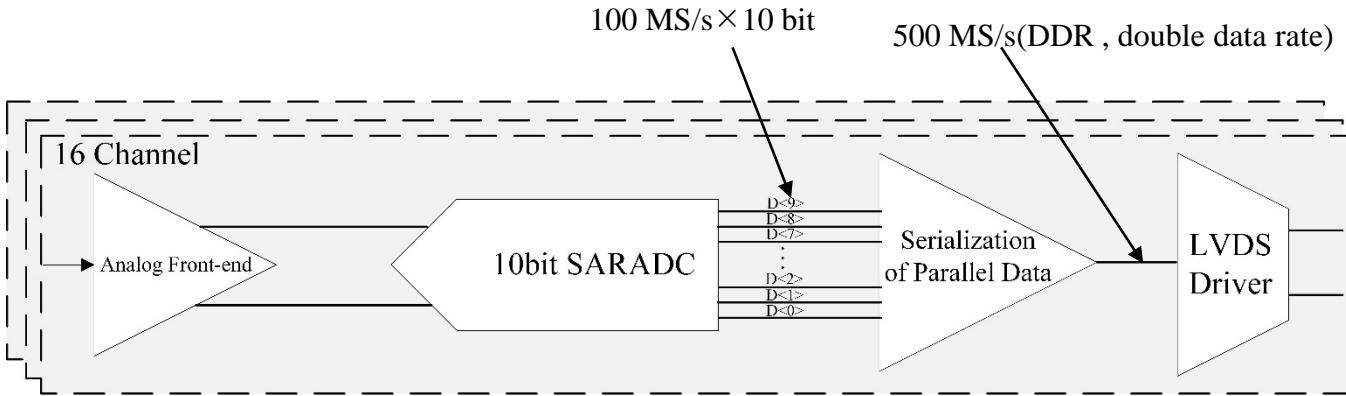
Layout of 16-ch TPC Readout ASIC



- The floor plan in layout :
 - The die size of 1950 μm x 2160 μm
 - Analog Front-End , SPI, SAR ADC, LVDS driver are supplied by separate power
- The ASIC have been taped out in November 6 ,2019 and will be evaluated in February,2020.

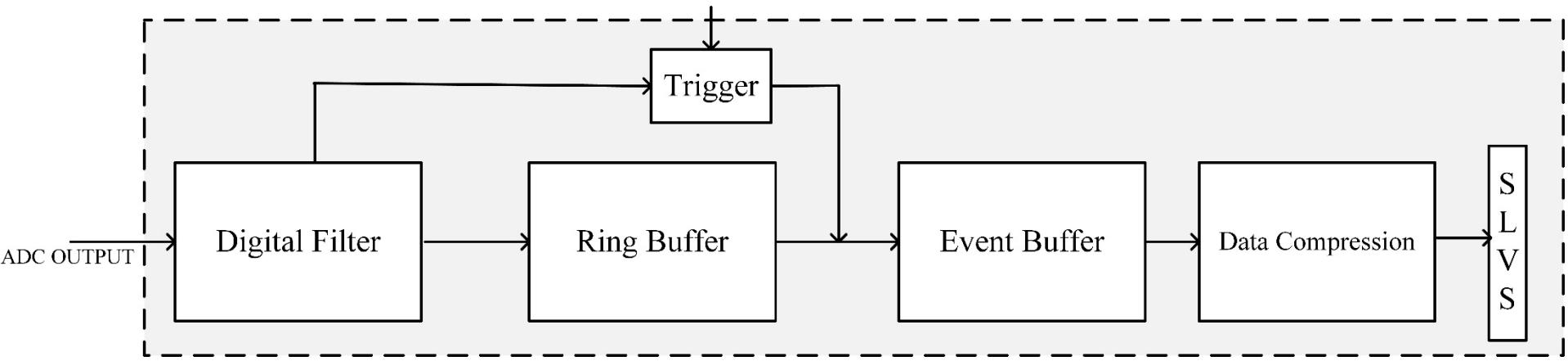
LVDS driver

Digital Filter and Data Compression



- The drawback of ADC data direct output:
 - Pile up due to the long decay tail of CR-RC shaper
 - The high data rate from LVDS driver
 - The high power consumption of LVDS driver
- The solution:
 - Digital trapezoidal filter balances the ballistic deficit and pile up
 - Compress the data via zero suppression , Huffman suppression , etc

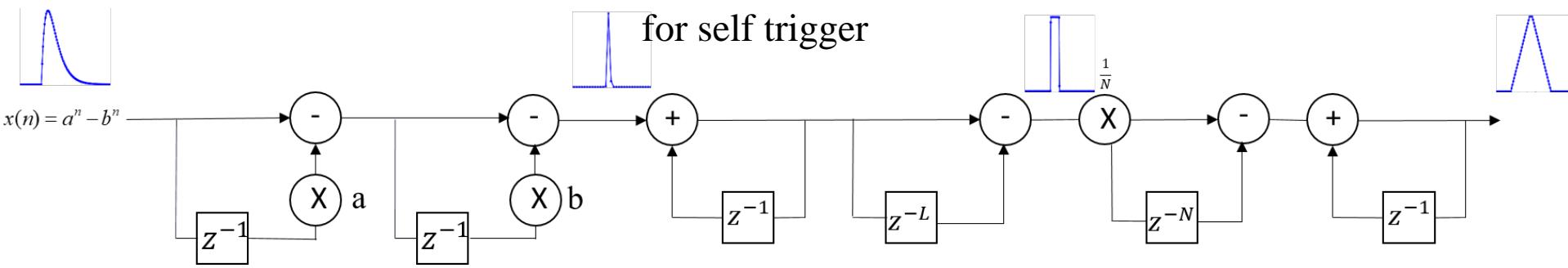
Preliminary Block Diagram of Digital Filter and Data Compression



Operating mode:

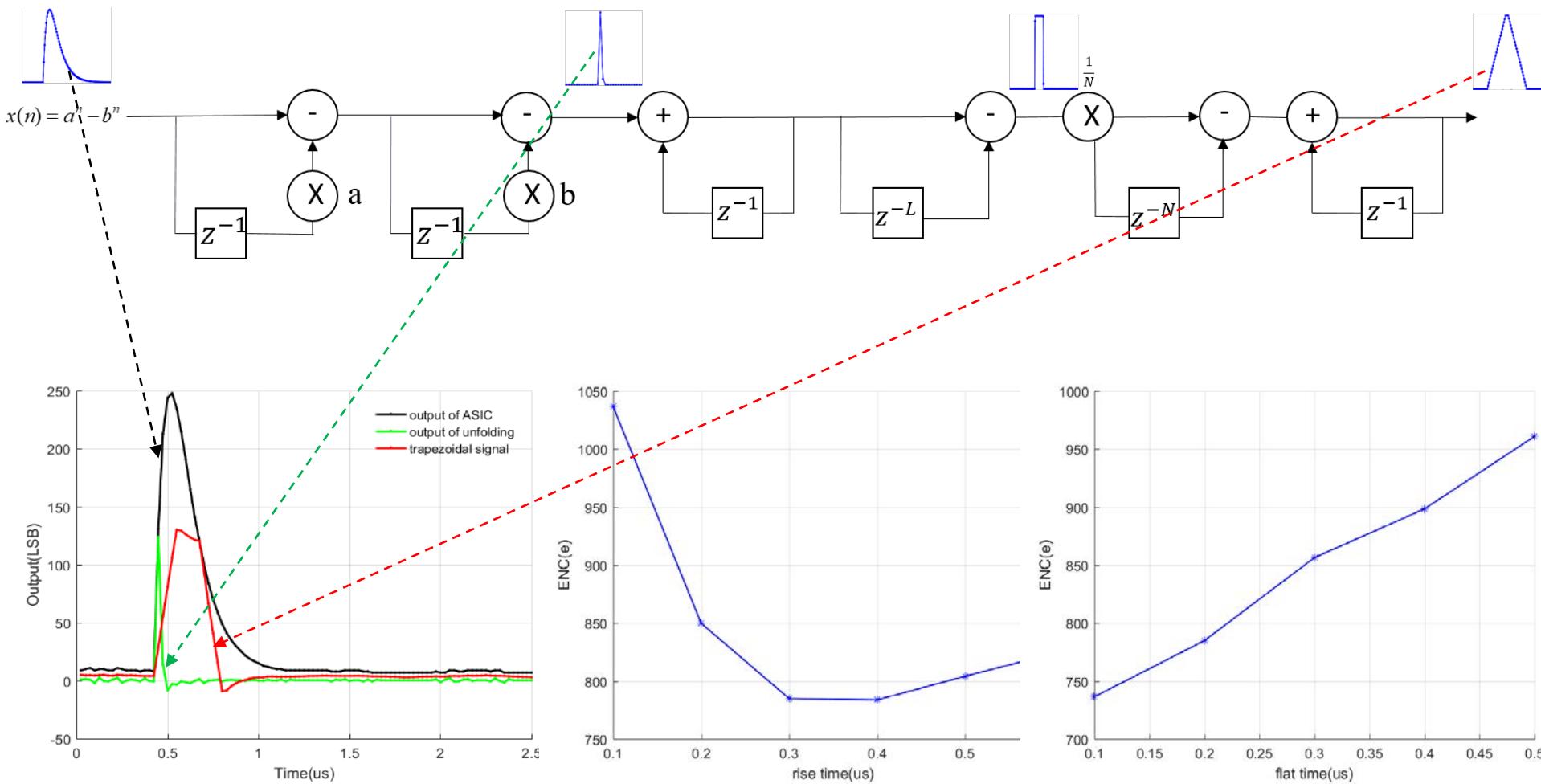
- Trigger mode: external trigger and self trigger
- Continuous operation

Digital Trapezoidal Filter



- The ballistic deficit can be avoided when the flat top is longer than detector charge collection time
- The waveform is symmetric, can achieve high SNR(signal to noise ratio)
- Hardware resource is low cost, can be well implemented on chip
 - 2 MUL (multiplications)
 - 6 ADD (additions) and SUB (subtractions)
 - some shift operations

Digital Trapezoidal Filter in MATLAB



When the flat top and rise time are suitable, the ENC can achieve minimum.

Summary

- 16 channel low power consumption and high integration ASIC for TPC readout have been developed
 - Based on the prototype ASICs of the first MPW run
 - adopting CR-RC shaper , achieving the analog part power consumption of 1.4 mW/channel, ENC:303 e @10 pF, 10 mV/fC,
 - Adopting SAR ADC, achieving the core power consumption of 1 mW/channel, ENOB:9.2 bit @50 MS/s

Future Plan

- The evaluation of the 16 channel lower power and high integration ASIC using signal generator and TPC prototype
- Development of the full function CEPC TPC readout ASIC
 - Low power digital filter and data compression in FPGA
 - Full function ASIC including AFE,SARADC,DSP design

Thank You